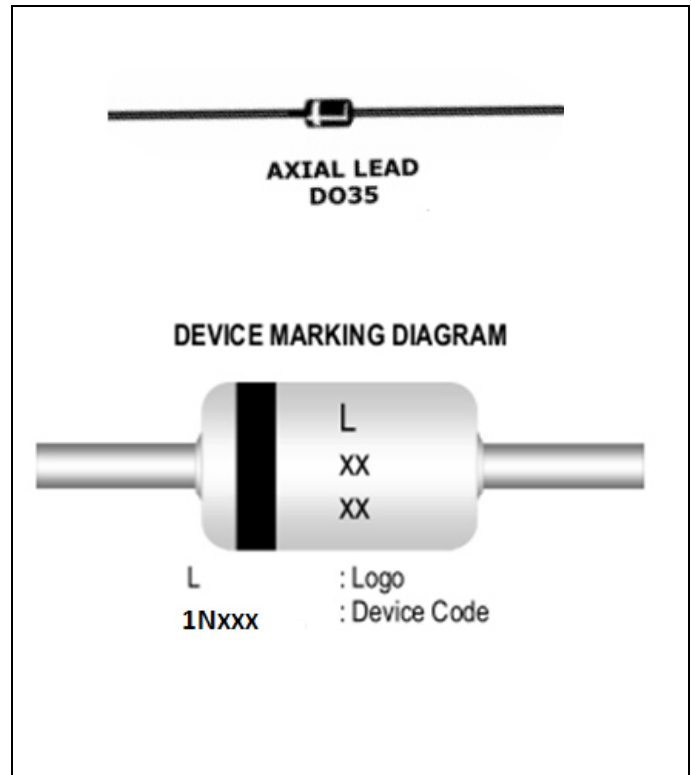
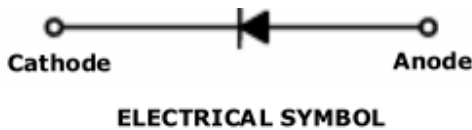


**Specification Features:**

- Fast Switching Device (T<sub>RR</sub> <4.0 nS)
- DO-35 Package (JEDEC)
- Through-Hole Device Type Mounting
- Hermetically Sealed Glass
- Compression Bonded Construction
- All External Surfaces Are Corrosion Resistant And Leads Are Readily Solderable
- RoHS Compliant
- Solder Hot Dip Tin (Sn) Terminal Finish
- Cathode Indicated By Polarity Band



**Absolute Maximum Ratings** T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
P <sub>D</sub>	Power Dissipation	500	mW
T <sub>STG</sub>	Storage Temperature Range	-65 to +150	°C
T <sub>J</sub>	Operating Junction Temperature	+150	°C
W <sub>IV</sub>	Working Inverse Voltage	75	V
I <sub>O</sub>	Average Rectified Current	150	mA
I <sub>FM</sub>	Non-repetitive Peak Forward Current	450	mA
I <sub>FSURGE</sub>	Peak Forward Surge Current (Pulse Width = 1.0 µsecond)	2	A

These ratings are limiting values above which the serviceability of the diode may be impaired.



# WEET Technology Company Limited

## High Speed Switching Diodes

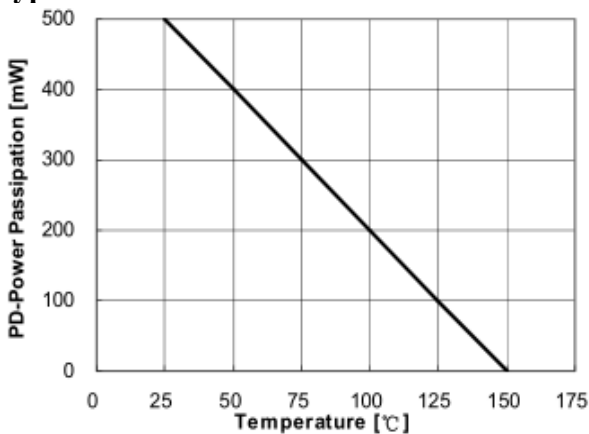
DO-35 1N4148

500 mW

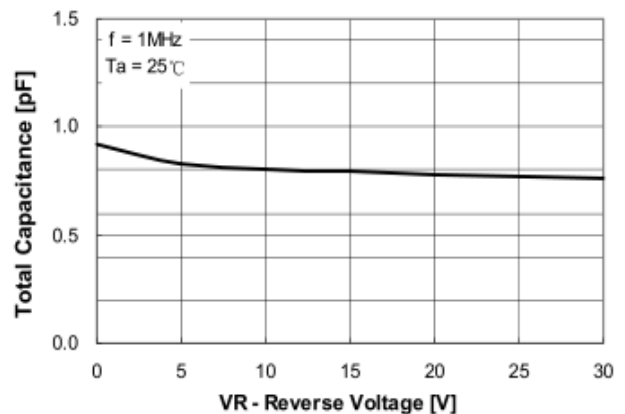
### Electrical Characteristics T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Limits		Unit
			Min	Max	
<b>B<sub>V</sub></b>	Breakdown Voltage	I <sub>R</sub> =100μA	100		Volts
		I <sub>R</sub> =5μA	75		
<b>I<sub>R</sub></b>	Reverse Leakage Current	V <sub>R</sub> =20V		25	nA
		V <sub>R</sub> =75V		5	μA
<b>V<sub>F</sub></b>	Forward Voltage	TC1N4448, TC1N914B I <sub>F</sub> =5mA	0.62	0.72	Volts
		TC1N4148 I <sub>F</sub> =10mA		1.0	
		TC1N4448, TC1N914B I <sub>F</sub> =100mA		1.0	
<b>T<sub>RR</sub></b>	Reverse Recovery Time	I <sub>F</sub> =10mA, V <sub>R</sub> =6V			nS
		R <sub>L</sub> =100Ω		4	
		I <sub>RR</sub> =1mA			
<b>C</b>	Capacitance	V <sub>R</sub> =0V, f=1MHz		4	pF

### Typical Characteristics



**Figure 1. Power Dissipation vs Ambient Temperature**  
Valid provided leads at a distance of 0.8mm from case are kept at ambient temperature



**Figure 2. Total Capacitance**

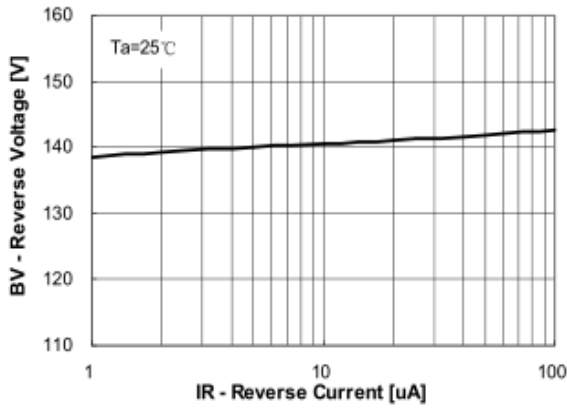


Figure 3. Reverse Voltage vs Reverse Current  
BV – 1.0uA to 100uA

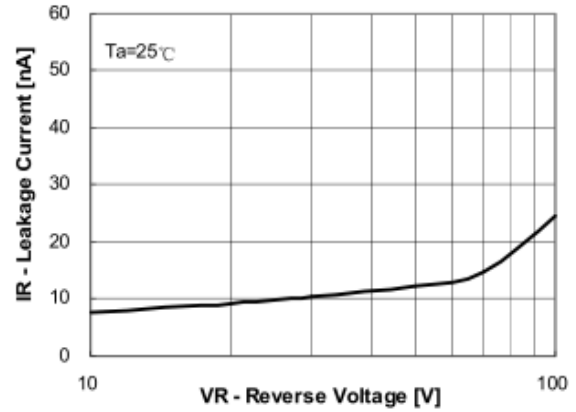


Figure 4. Reverse Current vs Reverse Voltage  
IR – 10V to 100V

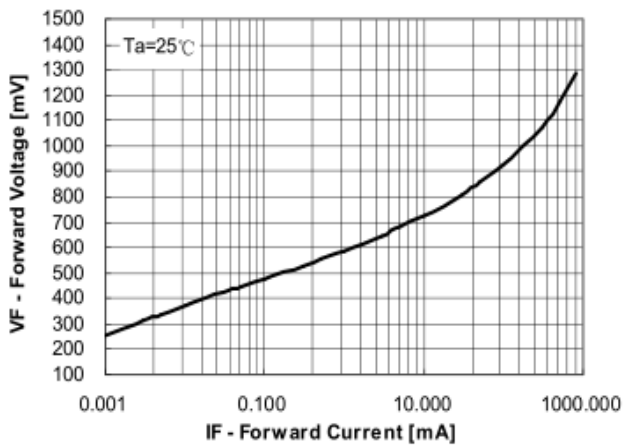


Figure 5. Forward Voltage vs Forward Current  
VF – 0.001mA to 800mA

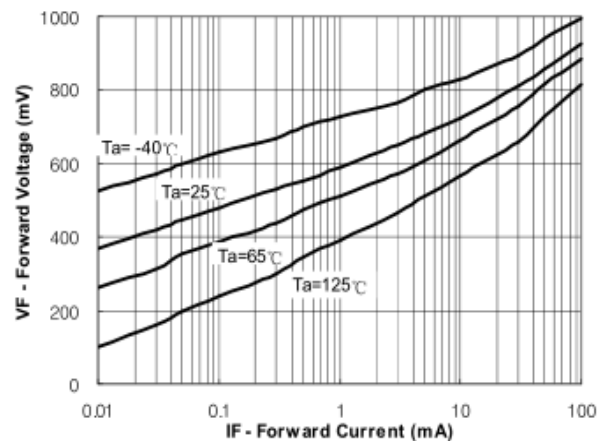
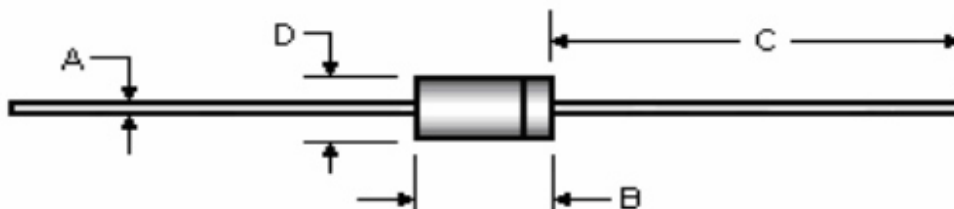


Figure 6. Forward Voltage vs Ambient Temperature  
VF – 0.01mA to 100mA (-40 to +125 Deg C)

### Package Outline





WEET Technology Company Limited  
High Speed Switching Diodes

DO-35 1N4148

500 mW

DIM	DO-35			
	Millimeters		Inches	
	Min	Max	Min	Max
A	0.46	0.55	0.018	0.022
B	3.05	4.00	0.120	0.157
C	25.40	38.10	1.000	1.500
D	1.53	2.00	0.060	0.079

**Notes:**

1. All dimensions are within JEDEC standard.
2. DO35 polarity denoted by cathode band.
3. The information presented in this document is for reference only.

Note: Specifications are subject to change without notice. For more detail and update, please visit our website.